



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638

ysbdt@szyoushang.cn

www.szyoushang.cn



企业微信二维码



企业QQ二维码

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D $T_A = 25^\circ C$
60V	80m Ω @ $V_{GS} = 10V$	7.90A
	150m Ω @ $V_{GS} = 4.5V$	5.75A

Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- DC-DC Converters
- Power management functions

Features and Benefits

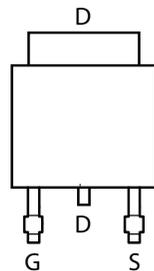
- Low on-resistance
- Fast switching speed
- "Green" component and RoHS compliant (Note 1)

Mechanical Data

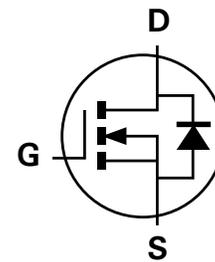
- Case: TO-252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.33 grams (approximate)



TOP VIEW



PIN OUT -TOP VIEW



Equivalent Circuit

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

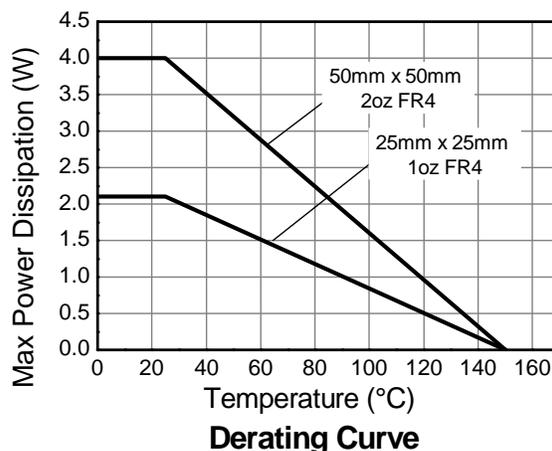
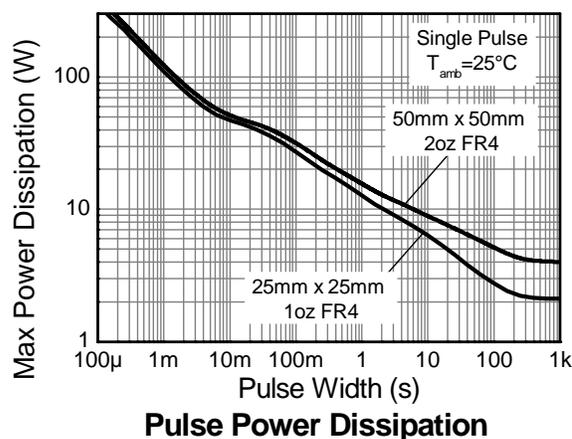
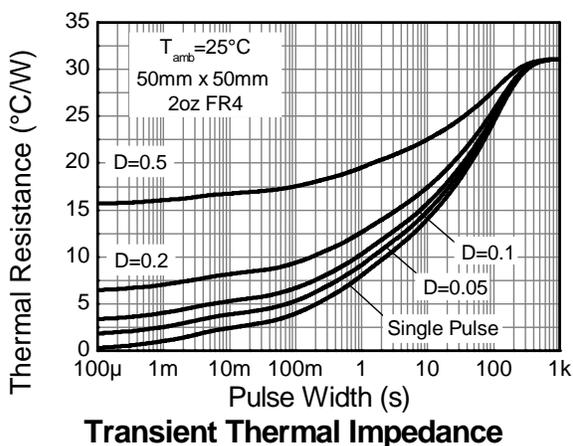
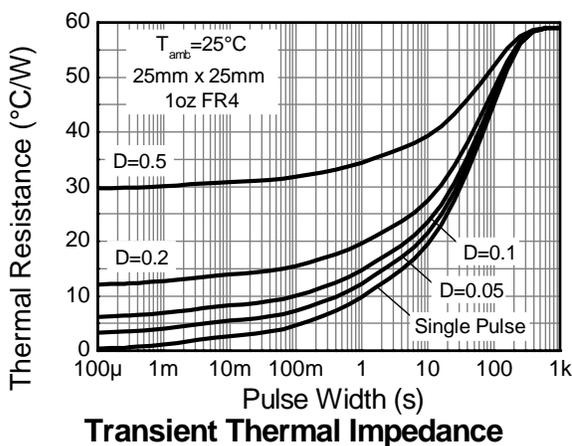
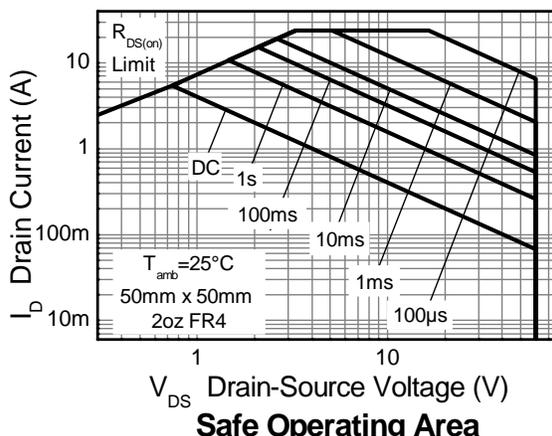
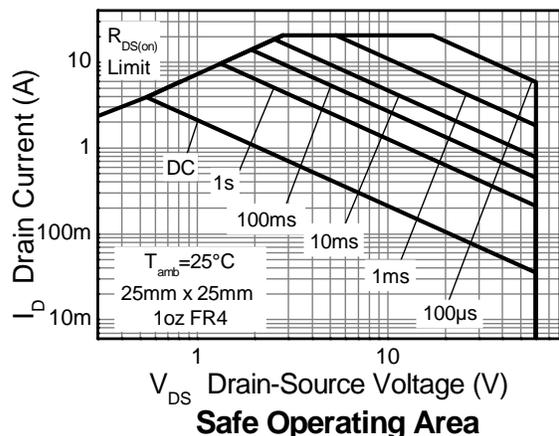
Characteristic		Symbol	Value	Unit	
Drain-Source voltage		V_{DS}	60	V	
Gate-Source voltage		V_{GS}	± 20	V	
Continuous Drain current	$V_{GS} = 10\text{V}$	(Note 3)	7.90	A	
		$T_A = 70^\circ\text{C}$ (Note 3)	6.30		
		(Note 2)	5.36		
Pulsed Drain current	$V_{GS} = 10\text{V}$	(Note 4)	I_{DM}	24.3	A
Continuous Source current (Body diode)		(Note 3)	I_S	9.0	A
Pulsed Source current (Body diode)		(Note 4)	I_{SM}	24.3	A

Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic		Symbol	Value	Unit
Power dissipation Linear derating factor	(Note 2)	P_D	4.13	W mW/ $^\circ\text{C}$
			33.0	
	(Note 3)		8.94	
	(Note 5)		71.5	
Thermal Resistance, Junction to Ambient	(Note 2)	$R_{\theta JA}$	2.12	$^\circ\text{C/W}$
	(Note 3)		16.9	
	(Note 5)		30.3	
Thermal Resistance, Junction to Lead	(Note 3)	$R_{\theta JL}$	14.0	$^\circ\text{C/W}$
	(Note 5)		59.1	
Operating and storage temperature range		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

- Notes:
2. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 3. Same as note 2, except the device is measured at $t \leq 10$ sec.
 4. Same as note 2, except the device is pulsed with $D = 0.02$ and pulse width 300 μs . The pulse current is limited by the maximum junction temperature.
 5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 6. Thermal resistance from junction to solder-point (at the end of the drain lead).

Thermal Characteristics

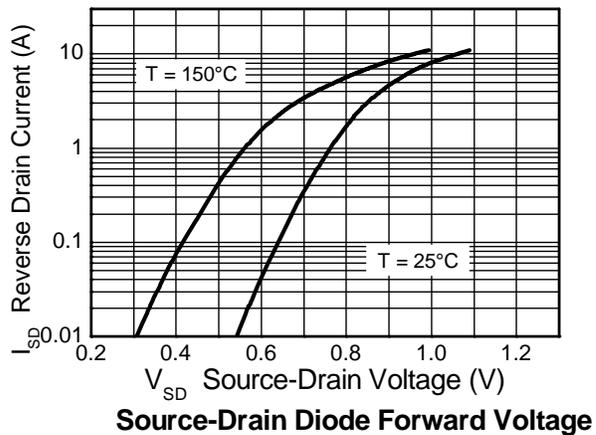
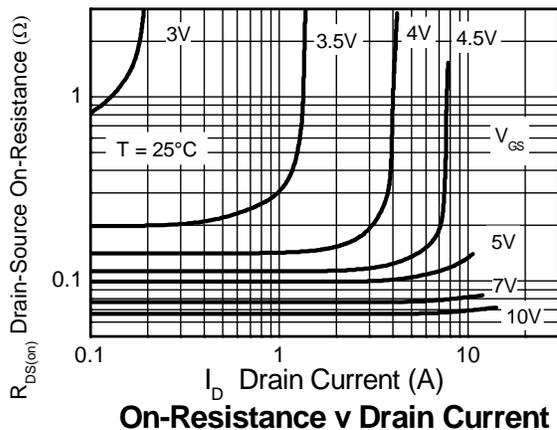
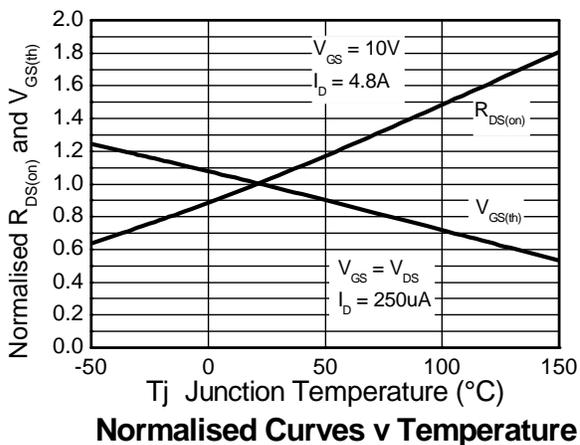
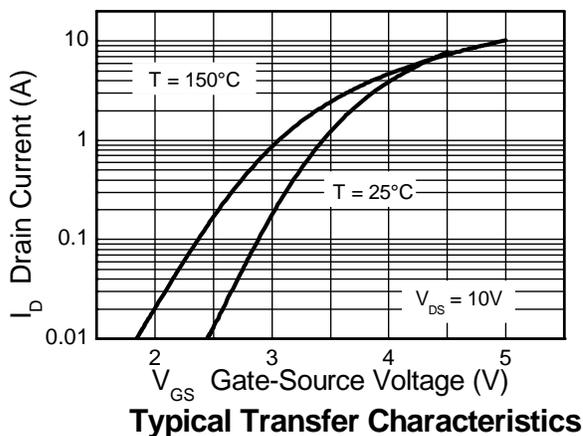
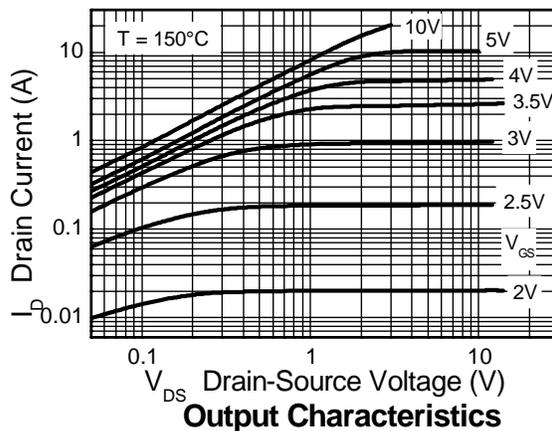
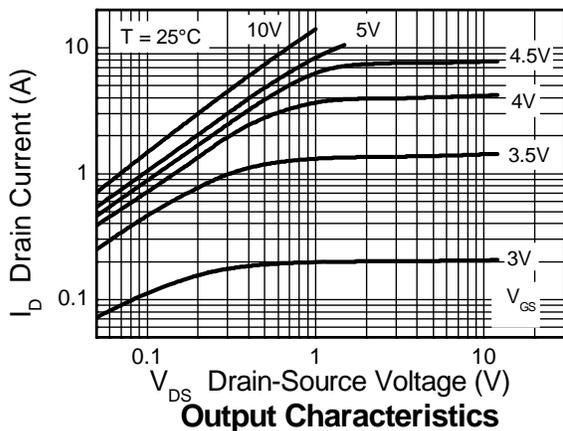


Electrical Characteristics @T_A = 25°C unless otherwise specified

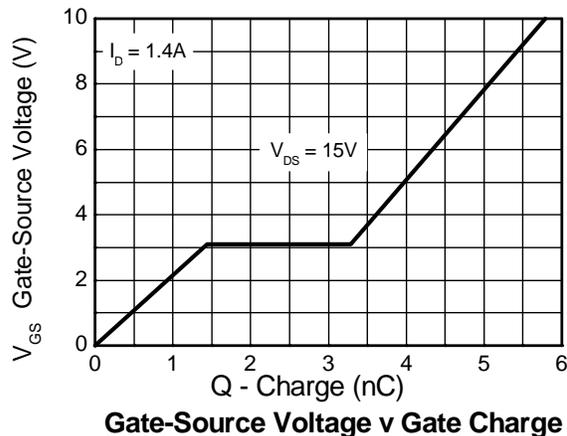
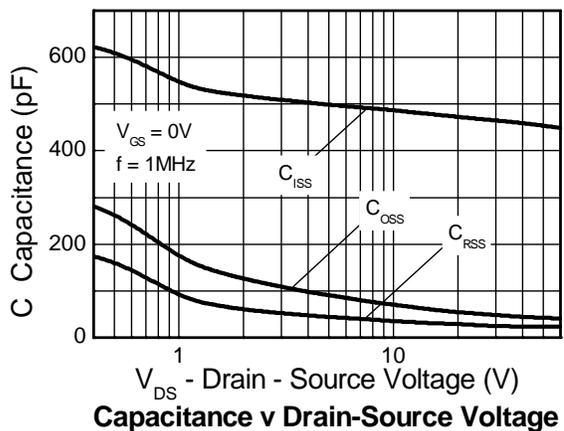
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	I _D = 250μA, V _{GS} = 0V
Zero Gate Voltage Drain Current	I _{DSS}	—	—	0.5	μA	V _{DS} = 60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(th)}	1.0	—	3.0	V	I _D = 250μA, V _{DS} = V _{GS}
Static Drain-Source On-Resistance (Note 7)	R _{DS(on)}	—	—	0.080	Ω	V _{GS} = 10V, I _D = 4.8A
				0.150		V _{GS} = 4.5V, I _D = 4.2A
Forward Transconductance (Notes 7 & 8)	g _{fs}	—	6.6	—	S	V _{DS} = 15V, I _D = 4.8A
Diode Forward Voltage (Note 7)	V _{SD}	—	0.88	0.95	V	I _S = 4.0A, V _{GS} = 0V
Reverse recovery time (Note 8)	t _{rr}	—	19.2	—	ns	I _S = 1.4A, di/dt = 100A/μs
Reverse recovery charge (Note 8)	Q _{rr}	—	30.3	—	nC	
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iSS}	—	459	—	pF	V _{DS} = 40V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{oss}	—	44.2	—	pF	
Reverse Transfer Capacitance	C _{rSS}	—	24.1	—	pF	
Total Gate Charge	Q _g	—	3.8	—	nC	V _{GS} = 4.5V
Total Gate Charge	Q _g	—	5.8	—	nC	V _{GS} = 10V
Gate-Source Charge	Q _{gs}	—	1.4	—	nC	
Gate-Drain Charge	Q _{gd}	—	1.9	—	nC	
Turn-On Delay Time (Note 9)	t _{D(on)}	—	2.6	—	ns	V _{DD} = 30V, V _{GS} = 10V I _D = 1.5A, R _G ≅ 6.0Ω
Turn-On Rise Time (Note 9)	t _r	—	2.1	—	ns	
Turn-Off Delay Time (Note 9)	t _{D(off)}	—	12.3	—	ns	
Turn-Off Fall Time (Note 9)	t _f	—	4.6	—	ns	

- Notes:
7. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%
 8. For design aid only, not subject to production testing.
 9. Switching characteristics are independent of operating junction temperatures.

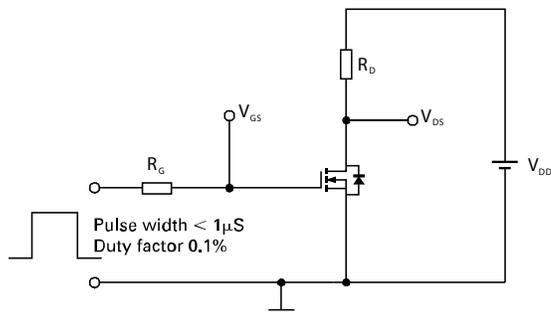
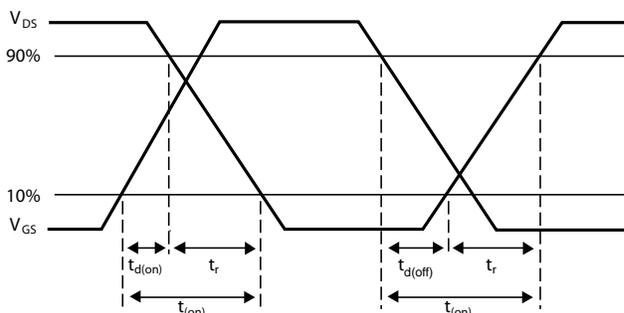
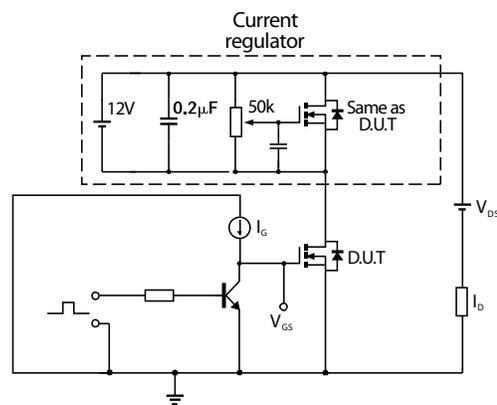
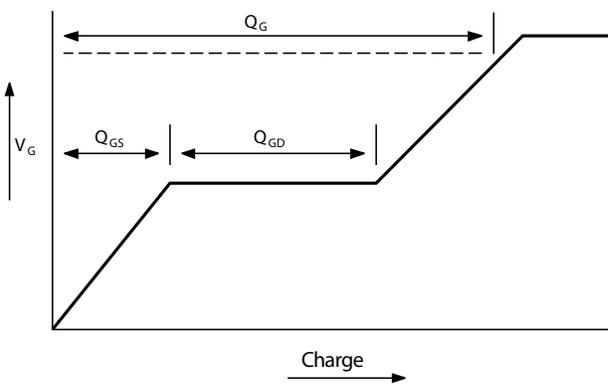
Typical Characteristics

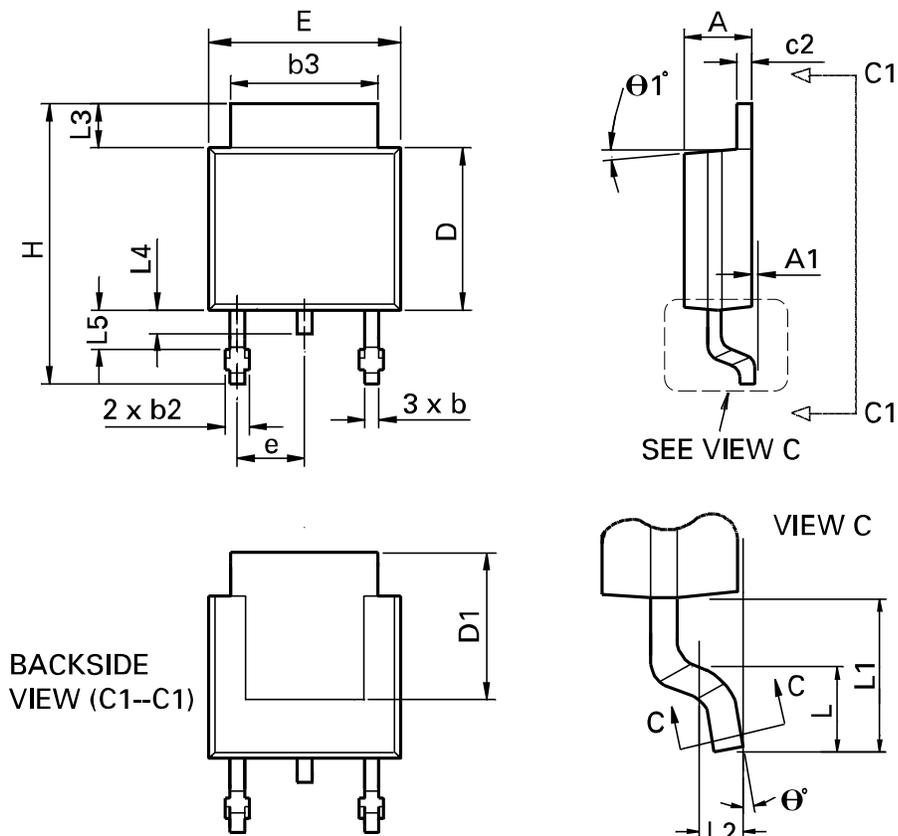


Typical Characteristics - continued



Test Circuits



Package Outline Dimensions


DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
A	0.086	0.094	2.18	2.39	e	0.090 BSC		2.29 BSC	
A1	-	0.005	-	0.127	H	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	L	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	L1	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	L2	0.020 BSC		0.508 BSC	
c	0.018	0.024	0.457	0.61	L3	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	L4	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	L5	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	$\theta 1^\circ$	0°	10°	0°	10°
E	0.250	0.265	6.35	6.73	θ°	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	-	-	-	-